

PD1900-35T00 InAsP PIN-PD

PD1900-35T00 is InAsP stepped layers type InAsP PIN-photodiode can be used at room temperature.

This PIN-photodiode is consists of a large chip with 0.35x0.35mm active area mounted on the TO-18 stem and is sealed by epoxy resin lens. These devices are designed to be easy of setting up optically with a wide angle of half sensitivity of $\pm 60^\circ$.

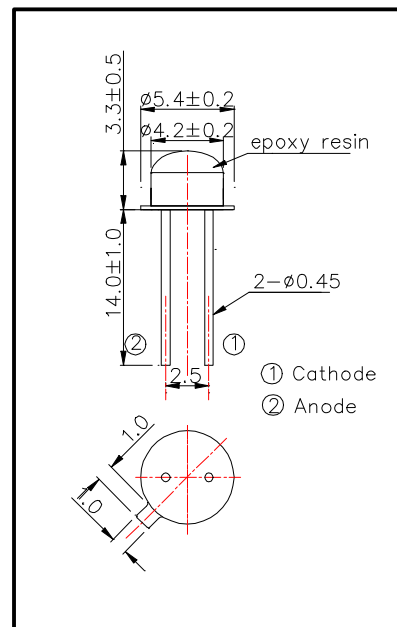
Features

- 1) Operative at Room Temperature
- 2) High Reliability
- 3) High Response

Specifications

- 1) Product Name InAsP PIN Photo-Diode
- 2) Type No. PD1900-35T00
- 3) Chip
 - (1) Active Area 0.35mmx0.35mm
- 4) Package
 - (1) Type TO-18
 - (2) Lens Epoxy Resin Lens

Outer dimension(Unit:mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	2	V
Operating Temperature	T_{OPR}	-20 ~ +90	$^\circ\text{C}$
Storage Temperature	T_{STG}	-30 ~ +100	$^\circ\text{C}$
Soldering Temperature	T_{SOL}	240	$^\circ\text{C}$

‡ Pulse Soldering condition: Soldering condition must be completed within 2 seconds at 240°C

Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	unit
Photo Responsivity	R_E	$V_R=0V, \lambda_P=1950\text{nm}$		1.2		A/W
Photo Current	I_L	$V_R=0V, \lambda_P=1950\text{nm}$		16		$\mu\text{A}(\pm 1)$
Dark Current	I_D	$V_R=1V$			5000	nA
Spectral Responsivity (Peak)	I_P	$V_R=0V$	1300		2100	nm
Half Angle of Sensitivity	$Q_{1/2}$	$V_R=0V$		± 60		deg.
Total Capacitance	C_T	$f=1\text{MHz}, V_R=1V$		20		pF
Rise/Fall Time(10%~90%)	t_r	$R_L=1K\Omega, V_R=1V$		5		ns
	t_f			5		ns

‡ Measured by Epitex' s calibrated tool

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